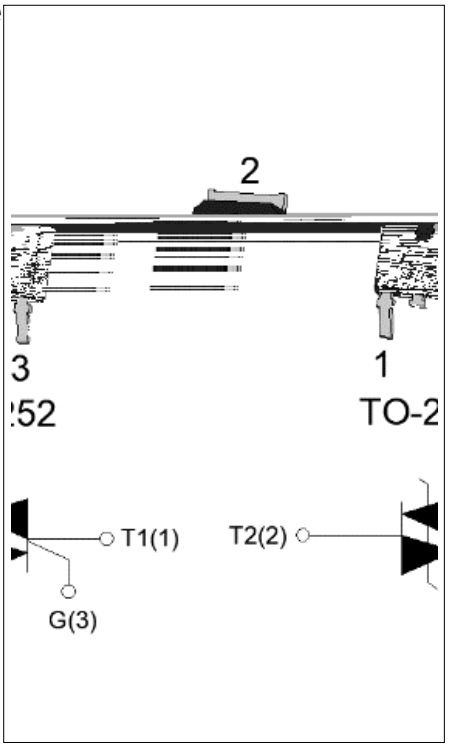
ACJT04K-1000CW 4A TRIAC

Rev.A.1.0

DESCRIPTION:

The ACJT04K-1000CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT04K-1000CW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-252 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM} /V_{RRM}	1000	V
I_{GT} / /	35/35/35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	1000	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	1000	V
RMS on-state current ($T_C \leq$ 100)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)	I_{TSM}	40	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)		44	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	8	A^2s
Critical rate of rise of on-state current (I_G=2 I_{GT} , f=100Hz , T_j=125)	dI/dt	100	A/μs
Peak gate current (t_p=20μs , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	3.75	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3KΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				60	
I_H	I_T =100mA		MAX.	35	mA
dV/dt	V_D=670V Gate Open T_j =125		MIN.	1600	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=125		MIN.	10	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	5	μs
t_{off}				70	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	1050	V

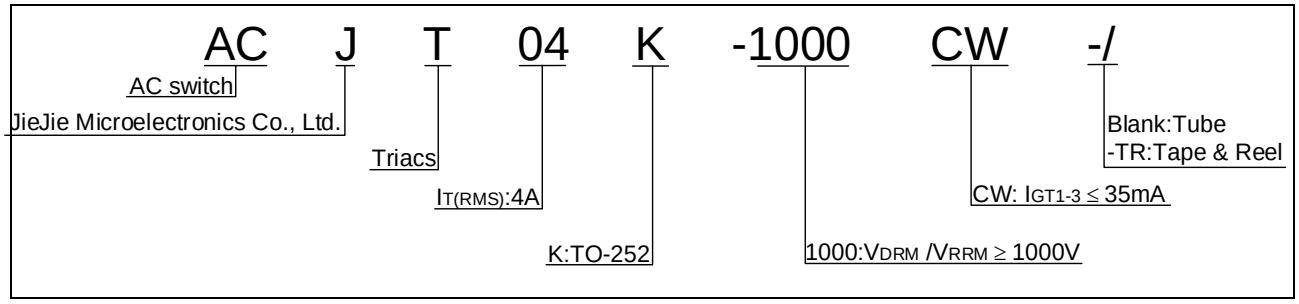
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =6A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.88	V
R_D	Dynamic resistance	T_j=125	82	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	8	μA
I_{RRM}		T_j=125	0.7	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit

ORDERING INFORMATION



MARKING

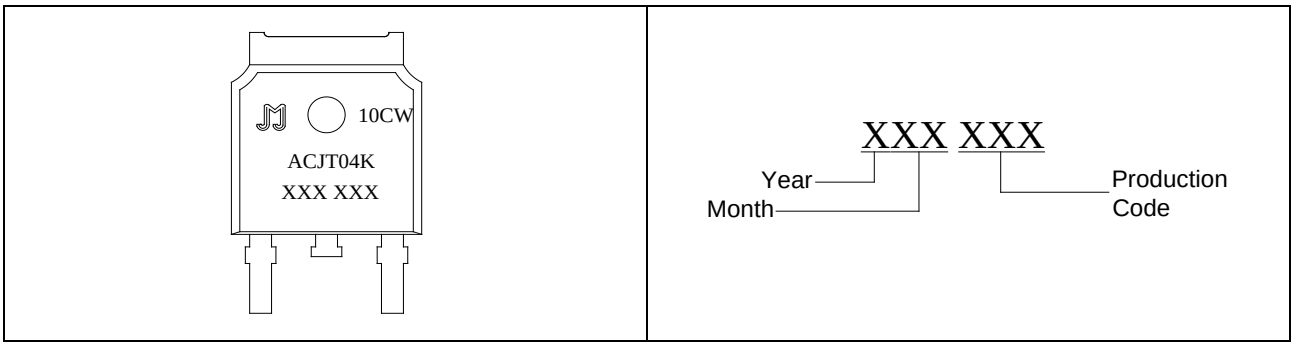


FIG.1 Maximum power dissipation versus RMS on-state current

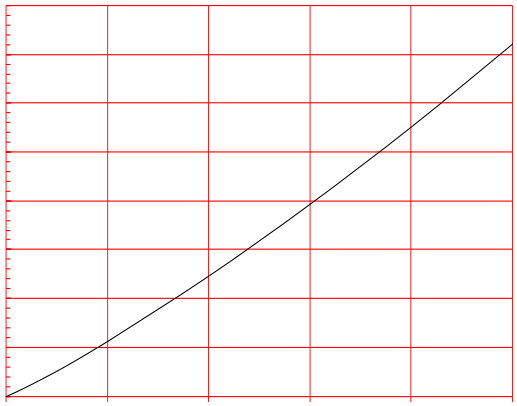


FIG.2: RMS on-state current versus case temperature

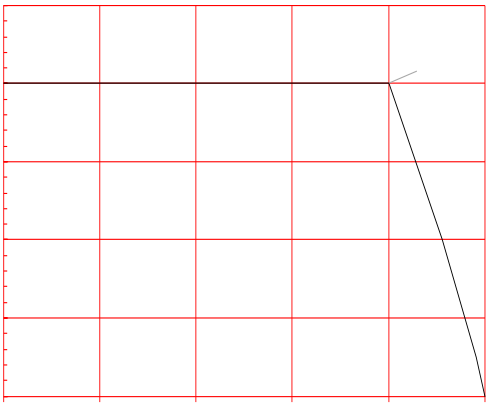


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm) (full cycle)

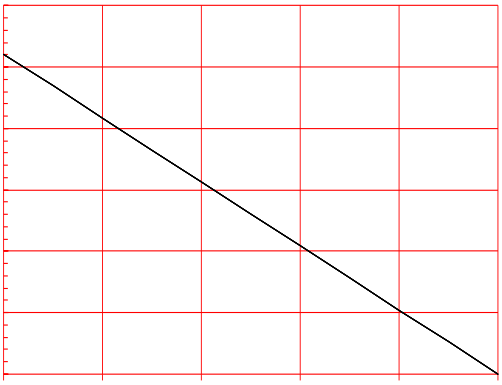


FIG.4: Surge peak on-state current versus number of cycles

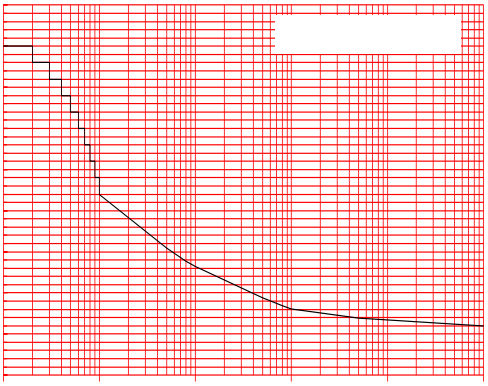


FIG.5: On-state characteristics

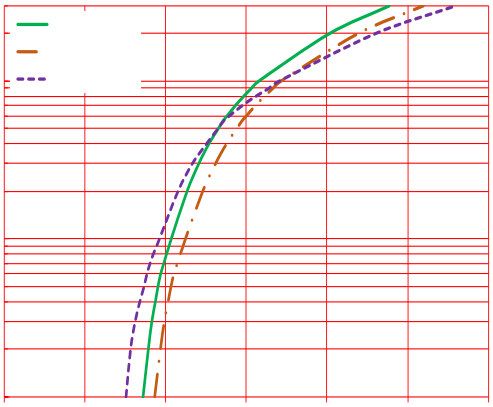


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/μs)

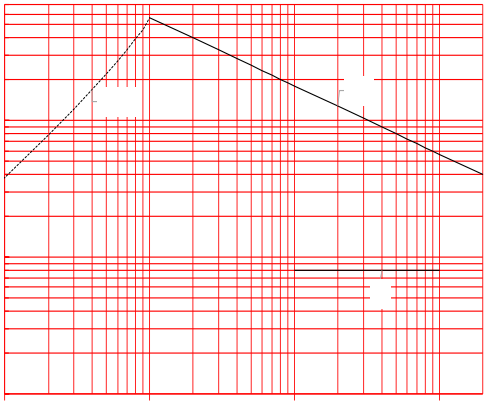


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

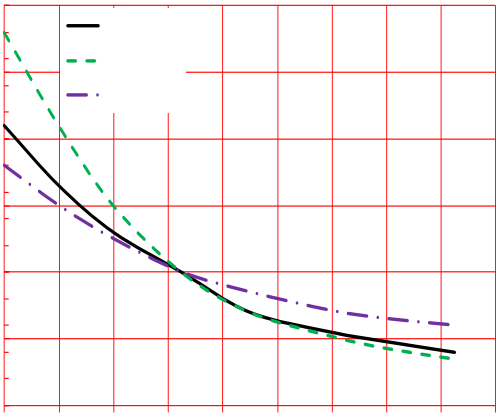
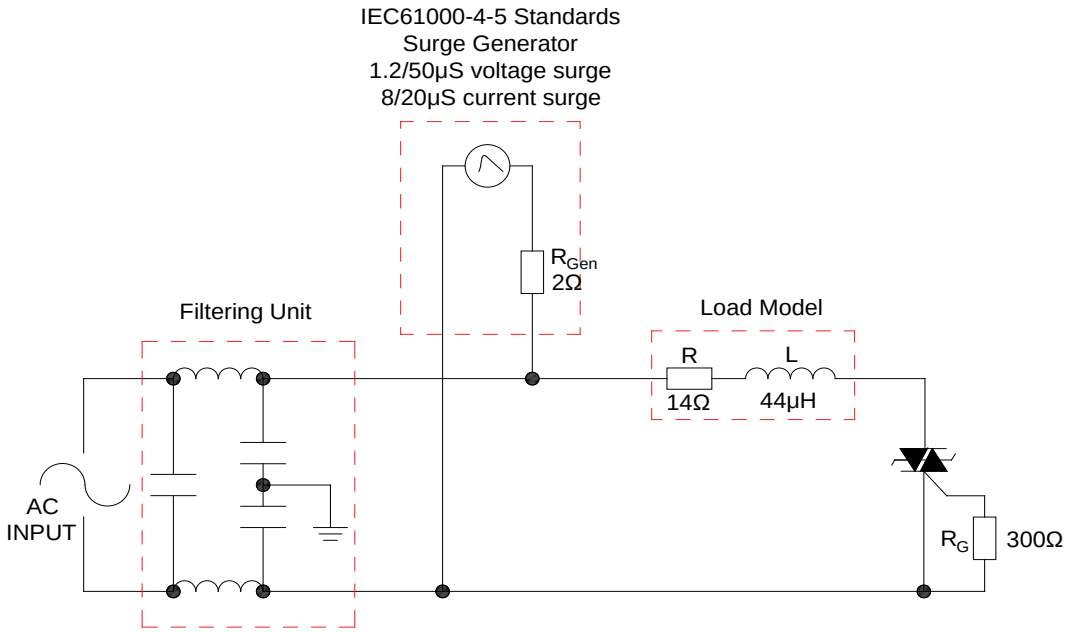
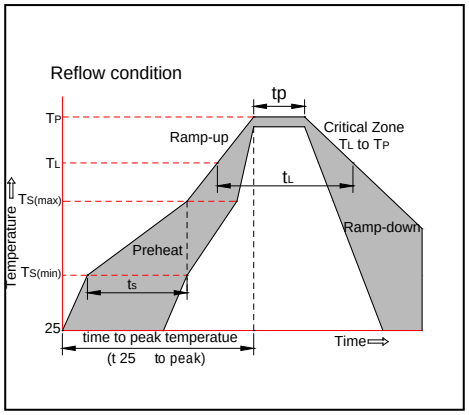


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5 of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25 to Peak Temp (T_P)		8 min. Max
Do not exceed		+260



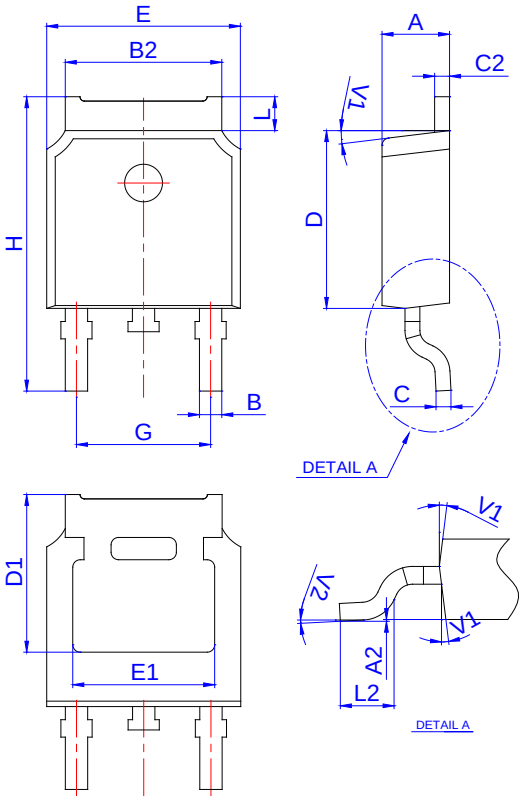
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT04K-1000CW	1000	35	TO-252	80	Tube
ACJT04K-1000CW-TR				2,500	Tape & Reel

Document Revision History

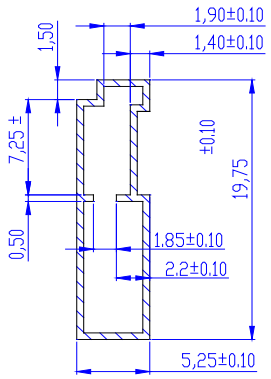
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

DELIVERY MODE



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